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- BiCMOS Design Substantially Reduces I_{CCZ}
- Output Ports Have Equivalent 25-Ω Resistors; No External Resistors Are Required
- Specifically Designed to Drive MOS DRAMs
- 3-State Outputs Drive Bus Lines or Buffer Memory Address Registers
- Flow-Through Architecture Optimizes PCB Layout
- Power-Up High-Impedance State
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015
- Package Options Include Plastic Small-Outline (DW) Packages, Ceramic Chip Carriers (FK) and Flatpacks (W), and Standard Plastic and Ceramic 300-mil DIPs (JT, NT)

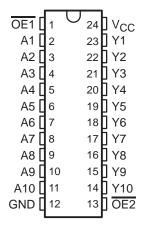
description

These 10-bit buffers and bus drivers are specifically designed to drive the capacitive input characteristics of MOS DRAMs. They provide high-performance bus interface for wide data paths or buses carrying parity.

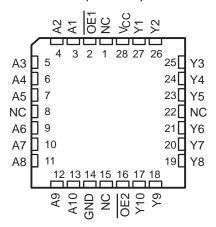
The 3-state control gate is a 2-input AND gate with active-low inputs so if either output-enable (OE1 or OE2) input is high, all ten outputs are in the high-impedance state. The outputs are also in the high-impedance state during power-up and power-down conditions. The outputs remain in the high-impedance state while the device is powered down.

The SN54BCT2827C is characterized for operation over the full military temperature range of -55°C to 125°C. The SN74BCT2827C is characterized for operation from 0°C to 70°C.

SN54BCT2827C . . . JT OR W PACKAGE SN74BCT2827C . . . DW OR NT PACKAGE (TOP VIEW)



SN54BCT2827C . . . FK PACKAGE (TOP VIEW)



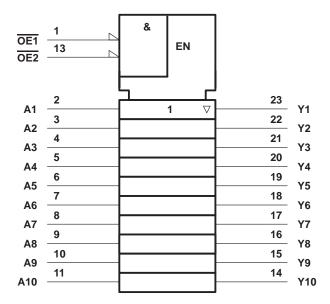
NC - No internal connection

FUNCTION TABLE

I	NPUTS	OUTPUT	
OE1	OE2	Α	Y
L	L	L	L
L	L	Н	Н
Н	X	Χ	Z
Х	Н	Χ	Z

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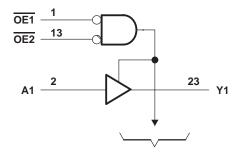
logic symbol[†]



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

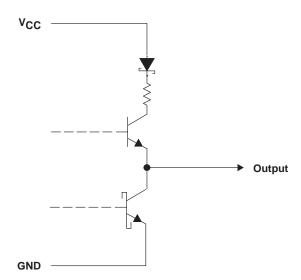
Pin numbers shown are for the DW, JT, NT, and W packages.

logic diagram (positive logic)



To Nine Other Channels

schematic of each output



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage range, V _{CC}	0.5 V to 7 V
Input voltage range, V _I (see Note 1)	0.5 V to 7 V
Voltage range applied to any output in the disabled or power-off state, V _O	-0.5 V to 5.5 V
Voltage range applied to any output in the high state, V _O	. -0.5 V to V_{CC}
Input clamp current, I _{IK}	30 mA
Current into any output in the low state	24 mA
Operating free-air temperature range: SN54BCT2827C	-55°C to 125°C
SN74BCT2827C	0°C to 70°C
Storage temperature range	-65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

recommended operating conditions

		SN5	4BCT28	27C	SN7	UNIT		
		MIN	NOM	MAX	MIN	NOM	MAX	UNIT
Vcc	Supply voltage	4.5	5	5.5	4.5	5	5.5	V
VIH	High-level input voltage	2			2			V
VIL	Low-level input voltage			0.8			0.8	V
liK	Input clamp current			-18			-18	mA
IOH	High-level output current			-1			-1	mA
loL	Low-level output current			12			12	mA
TA	Operating free-air temperature	-55		125	0		70	°C

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST	SN54	4BCT28	27C	SN7	UNIT			
PARAMETER	lESI C	TEST CONDITIONS					TYP [‡]	MAX	UNIT
VIK	$V_{CC} = 4.5 \text{ V},$	$I_{I} = -18 \text{ mA}$			-1.2			-1.2	V
Voн	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V},$	$I_{OH} = -1 \text{ mA}$	V _{CC} -2			V _{CC} -2			V
VOL	V _{CC} = 4.5 V	I _{OL} = 1 mA		0.15	0.5		0.15	0.5	V
VOL	VCC = 4.5 V	$I_{OL} = 12 \text{ mA}$		0.35	0.8		0.35	0.8	\ \ \
lozh	$V_{CC} = 5.5 \text{ V},$	$V_0 = 2.7 \text{ V}$			20			20	μΑ
lozL	$V_{CC} = 5.5 \text{ V},$	$V_0 = 0.5 V$			-20			-20	μΑ
lOL(sink)	V _{CC} = 4.5 V,	V _O = 2 V	50			50			mA
lı	V _{CC} = 5.5 V,	V _I = 7 V			0.1			0.1	mA
IH	V _{CC} = 5.5 V,	V _I = 2.7 V			20			20	μΑ
Ι _Ι Γ	V _{CC} = 5.5 V,	V _I = 0.5 V			-0.2			-0.2	mA
ΙΟ§	V _{CC} = 5.5 V,	V _O = 2.25 V	-30		-112	-30		-112	mA
^I CCL	V _{CC} = 5.5 V,	Outputs open		28	40		28	40	mA
lccz	$V_{CC} = 5.5 \text{ V},$	Outputs open		3.8	6		3.8	6	mA
Ci	V _{CC} = 5 V,	V _I = 2.5 V or 0.5 V		5			5		рF
Co	V _{CC} = 5 V,	V _I = 2.5 V or 0.5 V		8			8		pF

 $[\]ddagger$ All typical values are at V_{CC} = 5 V, T_A = 25°C.

[§] The output conditions have been chosen to produce a current that closely approximates one half of the true short circuit output current, IOS.



NOTE 1: The input negative-voltage rating may be exceeded if the input clamp current rating is observed.

SN54BCT2827C, SN74BCT2827C 10-BIT BUS/MOS MEMORY DRIVERS WITH 3-STATE OUTPUTS

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switching characteristics (see Note 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 5 V, C_{L} = 50 pF, R1 = 500 Ω, R2 = 500 Ω, T_{A} = 25°C			V_{CC} = 4.5 V to 5.5 V, C_L = 50 pF, R1 = 500 Ω, R2 = 500 Ω, T_A = MIN to MAX \dagger				UNIT		
			′BCT2827C			SN54BC	T2827C	SN74BCT2827C				
			MIN	TYP	MAX	MIN	MAX	MIN	MAX			
t _{PLH}	А	Y	0.9	3.6	5.2	0.9	6.6	0.9	6			
t _{PHL}	A		ĭ	r	'	2	5.1	7.2	2	8.2	2	7.8
^t PZH	ŌĒ	Y	2.8	5.6	8	2.8	10.7	2.8	10.7	ns		
t _{PZL}	OE	E Y	5	8.9	11	5	13.7	5	12.9	115		
^t PHZ	ŌĒ	Y	3.2	6.7	8.5	3.2	14	3.2	13	ns		
^t PLZ	OL .	1	2.7	5.3	10.5	2.7	11	2.7	10	115		

[†] For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions. NOTE 2: Load circuits and voltage waveforms are shown in Section 1.



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Advanced Search

PRODUCT FOLDER | PRODUCT INFO: FEATURES | DESCRIPTION | DATASHEETS | PRICING/AVAILABILITY/PKG APPLICATION NOTES | RELATED DOCUMENTS

PRODUCT SUPPORT: TRAINING

SN74BCT2827C, 10-Bit Bus/MOS Memory Drivers With 3-State Outputs

DEVICE STATUS: ACTIVE

PARAMETER NAME	SN74BCT2827C
Voltage Nodes (V)	5
Vcc range (V)	4.5 to 5.5
Input Level	TTL
Output Level	TTL
Output Drive (mA)	-1/12
tpd max (ns)	7.8
Static Current	40

Back to Top **FEATURES**

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DESCRIPTION ▲Back to Top

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TECHNICAL DOCUMENTS ▲Back to Top

To view the following documents, Acrobat Reader 4.0 is required.

To download a document to your hard drive, right-click on the link and choose 'Save'.

▲Back to Top DATASHEET

Full datasheet in Acrobat PDF: sn74bct2827c.pdf (74 KB,Rev.E) (Updated: 01/01/1991)

▲Back to Top **APPLICATION NOTES**

View Application Notes for <u>Digital Logic</u>

- Bus-Interface Devices With Output-Damping Resistors Or Reduced-Drive Outputs (Rev. A) (SCBA012A Updated: 08/01/1997)
- Designing With Logic (Rev. C) (SDYA009C Updated: 06/01/1997)
- Evaluation of Nickel/Palladium/Gold-Finished Surface-Mount Integrated Circuits (SZZA026 Updated: 06/20/2001)
- Implications of Slow or Floating CMOS Inputs (Rev. C) (SCBA004C Updated: 02/01/1998)
- Input and Output Characteristics of Digital Integrated Circuits (SDYA010 Updated: 10/01/1996)
- Live Insertion (SDYA012 Updated: 10/01/1996)
- Timing Differences of 10-pF Versus 50pF Loading (SCEA004 Updated: 11/01/1996)

RELATED DOCUMENT

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View Related Documentation for Digital Logic

- Logic Reference Guide (SCYB004, 1032 KB Updated: 10/23/2001)
- Logic Selection Guide Second Half 2002 (Rev. R) (SDYU001R, 4274 KB Updated: 07/19/2002)
- Military Semiconductors Selection Guide 2002 (Rev. B) (SGYC003B, 1648 KB Updated: 04/22/2002)

PRICING/AVAILABILITY/PKG ABack to Top														
DEVICE INFORMAT	ION							INVENTORY STAT 00 PM GMT, 26 S		REPORTED DISTRIBUTOR INVENTORY AS OF 3:00 PM GMT, 26 Sep 2002				
ORDERABLE DEVICE	<u>STATUS</u>	PACKAGE TYPE PINS	TEMP (°C)	PRODUCT CONTENT	BUDGETARY PRICING QTY \$US	STD PACK QTY	IN STOCK	IN PROGRESS QTY DATE	LEAD TIME	DISTRIBUTOR COMPANY REGION	IN STOCK	PURCHASE		
SN74BCT2827CDW	ACTIVE	SOP (DW) 24	0 TO 70	View Contents	1KU 1.75	25	775	100 24 Sep	12 WKS					
								>10k 14 Oct						
SN74BCT2827CDWR	ACTIVE	SOP (DW) 24	0 TO 70	View Contents	1KU 1.78	2000	<u>N/A*</u>	>10k 09 Oct	12 WKS					
								>10k 11 Dec						
SN74BCT2827CNSR	ACTIVE	$\frac{\text{SOP}}{\text{(NS)}}$ 24		<u>View Contents</u>	1KU 1.78	2000	<u>N/A*</u>	8560 14 Oct	12 WKS					
								>10k 21 Oct						
								>10k 28 Oct						
								>10k 04 Nov						
SN74BCT2827CNT	ACTIVE	PDIP 24	0 TO 70	<u>View Contents</u>	1KU 1.75	15	270	570 19 Sep	12 WKS					
								9169 09 Oct						
								>10k 16 Oct						

Table Data Updated on: 9/26/2002

$\underline{Products} \mid \underline{Applications} \mid \underline{Support} \mid \underline{TI\&ME}$

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